

Amendments to the Specification

Please replace the paragraph beginning on page 25, line 8, with the following rewritten paragraph.

In an embodiment, the method may include altering a parameter of an instrument coupled to a process tool in response to at least one of the properties of an insulating film such as capacitance, dielectric constant, and/or thickness of the insulating film using a feedback control technique, as shown in step 78 of Fig. 7, or a feedforward control technique, as shown in step 79 of Fig. 7. The process tool may include, but is not limited to, a chemical vapor deposition (“CVD”) tool, a physical vapor deposition (“PVD”) tool, an atomic layer deposition (“ALD”) tool, and a thermal growth tool. In this manner, a parameter of an instrument coupled to a process tool may be altered for forming the insulating film on additional substrates. The process tool may also include a process tool used for further processing of the substrate on which the measured insulating film is formed. For example, such a process tool may include a chemical-mechanical polishing (“CMP”) tool. In this manner, a parameter of an instrument coupled to a process tool may be altered for further processing of the substrate on which the measured insulating film is formed. In a further embodiment, a processor as described herein may be coupled to the process tool and may be configured to alter a parameter of an instrument coupled to the process tool in response to at least one of the properties of the insulating film using a feedback control technique or a feedforward control technique.